

KSC5025

High Voltage and High Reliabilty

- High Speed Switching
- Wide SOA



NPN Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	800	V
V _{CEO}	Collector-Emitter Voltage	500	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current (DC)	15	Α
I _{CP}	Collector Current (Pulse)	25	Α
I _B	Base Current	4	Α
P _C	Collector Dissipation (T _C =25°C)	100	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C} = 1 \text{mA}, I_{E} = 0$	800			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{C} = 5mA, I_{B} = 0$	500			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	7			V
V _{CEX} (sus)	Collector-Emitter Sustaining Voltage	$I_C = 5A$, $I_{B1} = -I_{B2} = 2A$ $L = 500\mu H$, Clamped	500			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 500V, I_{E} = 0$			10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			10	μΑ
h _{FE1}	DC Current Gain	$V_{CE} = 5V, I_{C} = 1.2A$	15		50	
h _{FE2}		$V_{CE} = 5V, I_{C} = 6A$	8			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 6A, I_B = 1.2A$			1	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 6A, I_B = 1.2A$			1.5	V
C _{ob}	Output Capacitance	$V_{CB} = 10V, I_E = 0, f = 1MHz$		160		pF
f _T	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 1.2A$		18		MHz
t _{ON}	Turn On Time	V _{CC} = 200V			0.5	μs
t _{STG}	Storage Time	$I_C = 5I_{B1} = -2.5I_{B2} = 7A$			3	μs
t _F	Fall Time	$R_L = 28.6\Omega$			0.3	μs

h_{FE} Classificntion

Classification	R	0	Y
h _{FE1}	15 ~ 30	20 ~ 40	30 ~ 50

Typical Characteristics

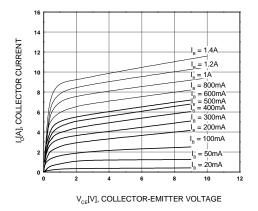


Figure 1. Static Characteristic

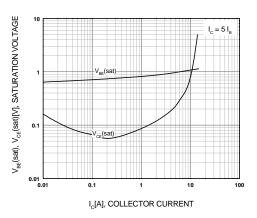


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

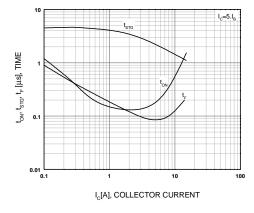


Figure 5. Switching Time

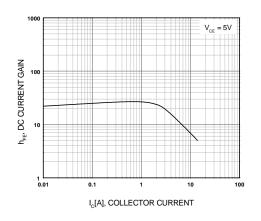


Figure 2. DC current Gain

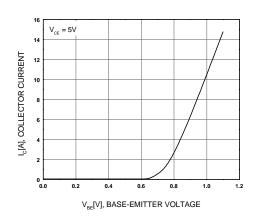


Figure 4. Base-Emitter On Voltage

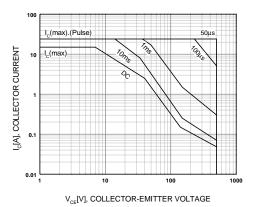


Figure 6. Safe Operating Area

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Typical Characteristics (Continued)

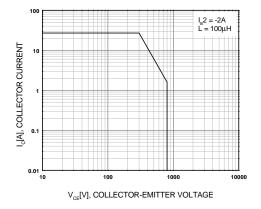


Figure 7. Reverse Bias Safe Operating Area

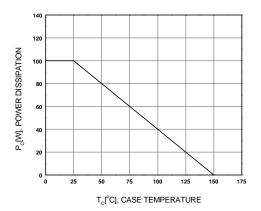
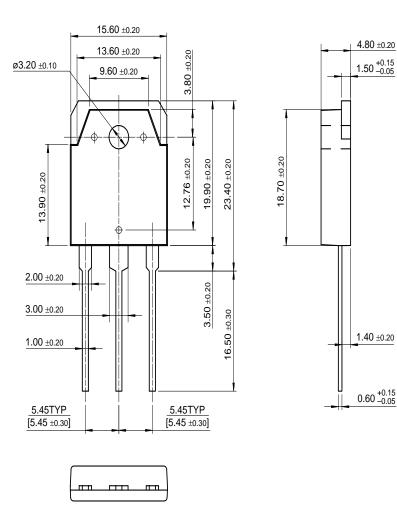


Figure 8. Power Derating

Package Dimensions

TO-3P



Dimensions in Millimeters

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